

1.	Realization of the Kohn's theorem in Ge/Si quantum dots with hole gas: Theory and experiment.	печ. Ста	<i>Nanomaterials</i> 9(1), 56 (2019). https://doi.org/10.3390/nano9010056 Impact Factor 4.034 Q1	14 стр.	Hayk A. Sarkisyan, David B. Hayrapetyan, Lyudvig S. Petrosyan, Eduard M. Kazaryan, Anton N. Sofronov, Roman M. Balagula, Dmitry A. Firsov, Leonid E. Vorobjev, Alexander A. Tonkikh.
2.	Terahertz Optical Transmission Of Charged Ge/Si Quantum Dots.	печ. Ста	<i>43rd International Conference on Infrared, Millimeter, and Terahertz Waves, 2018. IRMMW-THz № 8510315</i> doi: 10.1109/IRMMW-THz.2018.8510315 .	2 стр.	R.M.Balagula, A.N.Sofronov, D.A.Firsov, L.E.Vorobjev, A.A.Tonkikh, H.A.Sarkisyan, D.B.Наурапетыан, E.M.Kazaryan.
3.	Поглощение излучения дальнего инфракрасного диапазона квантовыми точками Ge/Si. Absorption of Far-Infrared Radiation in Ge/Si Quantum Dots.	печ. Ста	<i>Физика и техника полупроводников</i> 52(1), 63-67 (2018). 10.21883/FTP.2018.01.45320.8655 <i>Semiconductors</i> 52(1), 59-63 (2018). 10.1134/S1063782618010220	5 стр.	А.Н.Софронов, Р.М.Балагула, Д.А.Фирсов, Л.Е.Воробьев, А.А.Тонких, А.А.Саркисян, Д.Б.Айрапетян, Л.С.Петросян, Э.М.Казарян. A.N.Sofronov, R.M.Balagula, D.A.Firsov, L.E.Vorobjev, A.A.Tonkikh, H.A.Sarkisyan, D.B.Наурапетыан, L.S.Petrosyan, E.M.Kazaryan.
4.	Charge carrier kinetics in GeSi/Si quantum dots probed by mid-infrared radiation.	печ. Ста	<i>Journal of Physics: Conf. Series</i> 864, 012069 (2017). <i>33rd International Conference on the Physics of Semiconductors</i> . http://dx.doi.org/10.1088/1742-6596/864/1/012069	4 стр.	A.N.Sofronov, L.E.Vorobjev, D.A.Firsov, R.M.Balagula, A.A.Tonkikh.
5.	Temperature depopulation of the GeSi/Si quantum dots with non-equilibrium charge carriers.	печ. Ста	<i>Superlattices and Microstructures</i> 107, 228-233 (2017). http://dx.doi.org/10.1016/j.spmi.2017.04.028 Q2	6 стр.	A.N.Sofronov, L.E.Vorobjev, D.A.Firsov, R.M.Balagula, A.A.Tonkikh.

